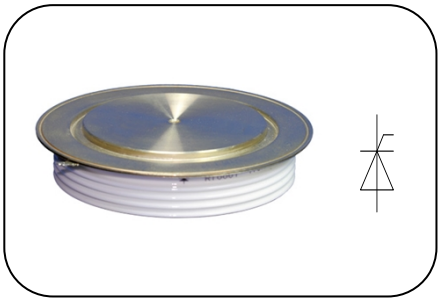


Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Pulsed power
- Ignitron Replacement

Part No. H125KMM-KT110cT		
I_{PK}	**250kA**	
V_{DRM},V_{RRM}	**4200V**	**4500V**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
I_{pk}	Pulse peak on-state current	Singie pulse sine wave tp：500μs	110			250	kA
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled，T_C=70°C	110			4100	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms	110	4200		4500	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	110			500	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}	110			72	kA
I^2t	I^2t for fusing coordination					25920	A^2s*10^3
V_{TM}	Peak on-state voltage	I_{TM}=5000A, F=120kN, tp=10ms	25			1.65	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM}	110			2000	V/μs
di/dt	Critical rate of rise of on-state current	Gate pulse t_r ≤0.5μs I_{GM}=1.5A	110			3000	A/μs
Q_{rr}	Recovery charge	I_{TM}=2000A, tp=4000μs, di/dt=-20A/μs, V_R=100V	110		17000		μC
I_{GT}	Gate trigger current	V_A=12V, I_A=1A	25	40		300	mA
V_{GT}	Gate trigger voltage			0.8		3.5	V
I_H	Holding current			20		1000	mA
I_L	Latching current					1000	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}	110	0.25			V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180^0 sine, double side cooled Clamping force 120 kN				0.004	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.001	°C /W
F_m	Mounting force			110		140	kN
T_{vj}	Junction temperature			-40		110	°C
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				2620		g
Outline	KT110cT						

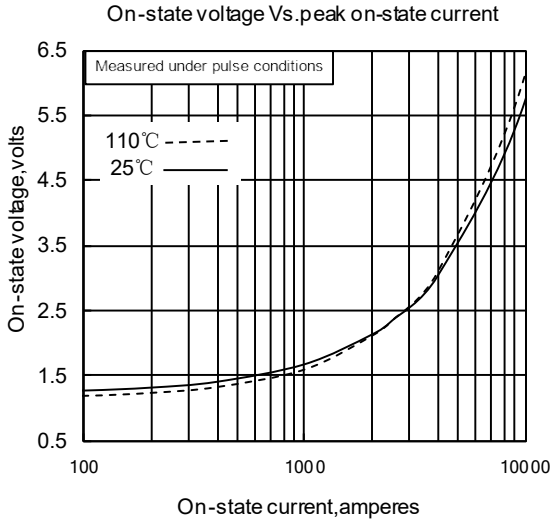


Fig. 1

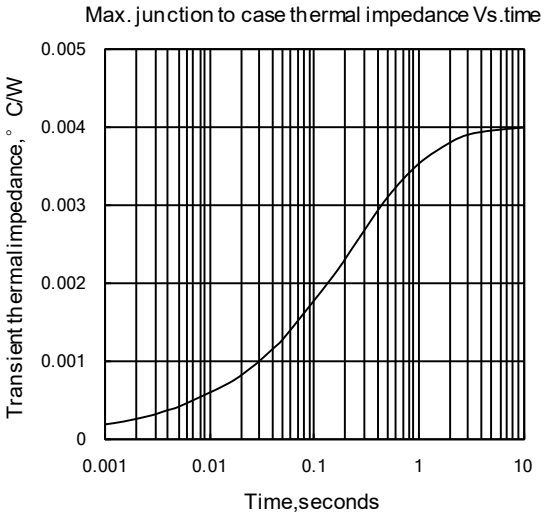


Fig. 2

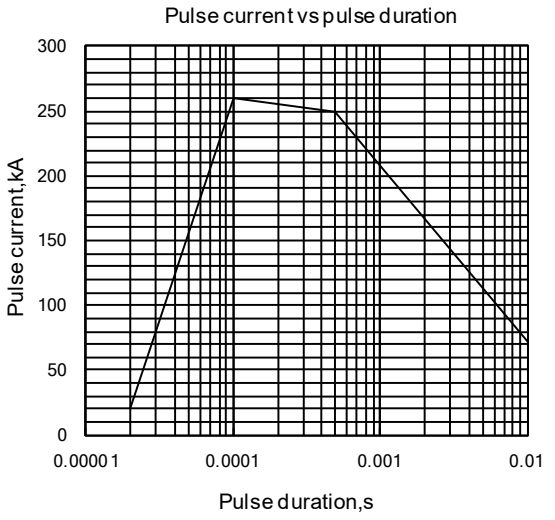


Fig. 3

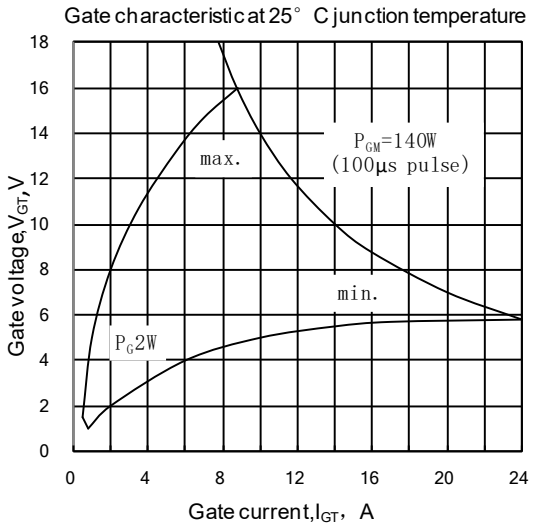


Fig. 4

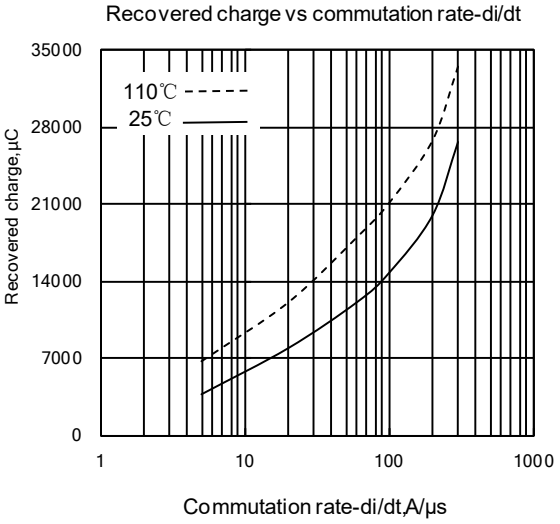


Fig. 5

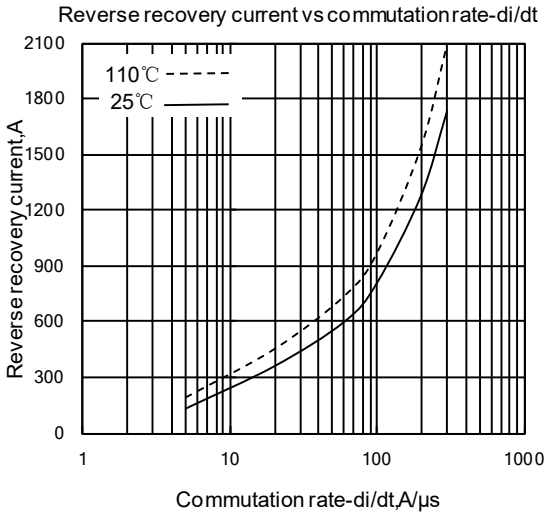
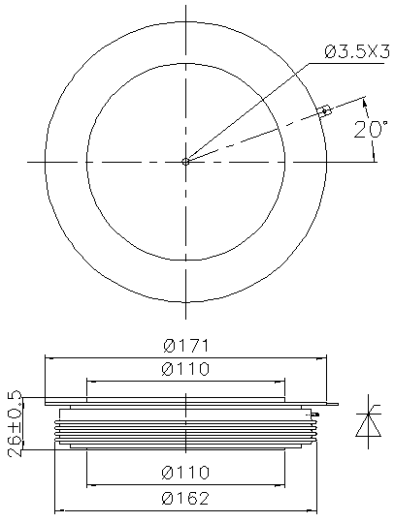


Fig. 6

Outline:



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